

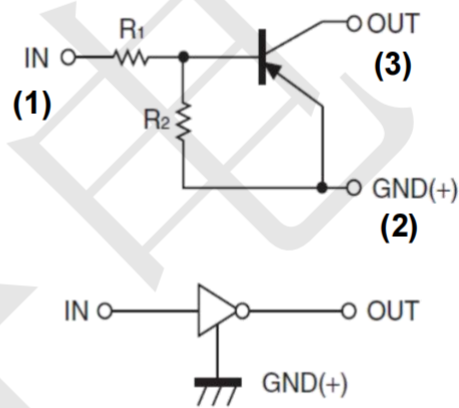
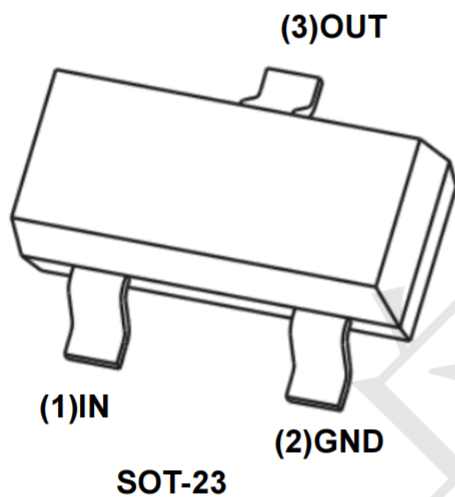
### Product Summary

- VCC = -50V
- IC = -100mA
- R1 = 1kΩ
- R2 = 1kΩ

### Features

- Built-in bias resistors
- making device design easy
- almost completely eliminating parasitic effects

### Circuit diagram and pin information



### Absolute Maximum Ratings

(Ta=25°C unless otherwise specified)

PARAMETER	SYMBOL	LIMIT	UNIT
Supply Voltage	VCC	-50	V
Input Voltage	VIN	-10~+10V	V
Collector current	IC	-100	mA
Power Total Dissipation @ TA=25°C	PD	200	mW
Maximum Operating Junction Temperature	TJ	+150	°C
Storage Temperature Range	TSTG	-55 to +150	°C

### Electrical Characteristics

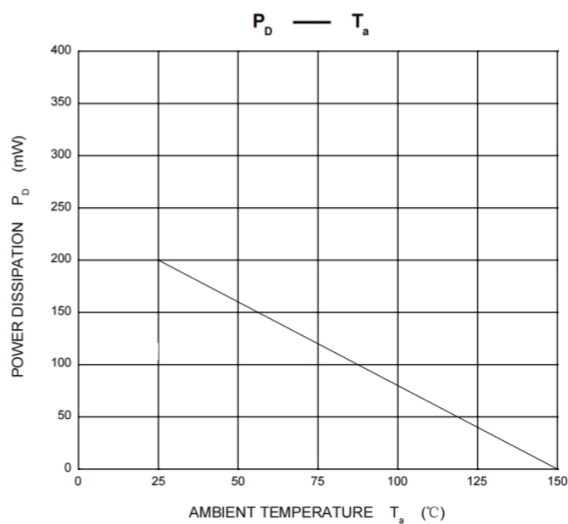
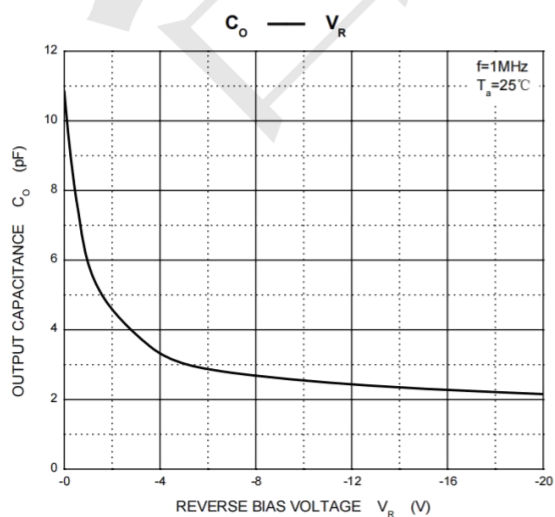
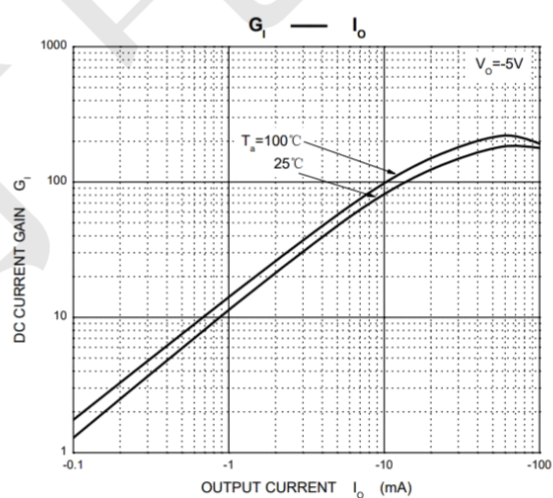
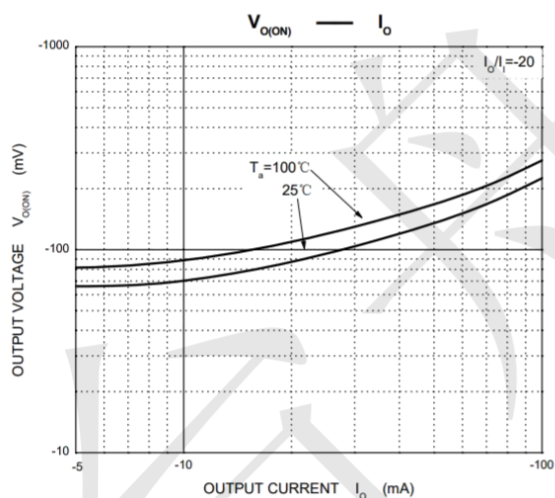
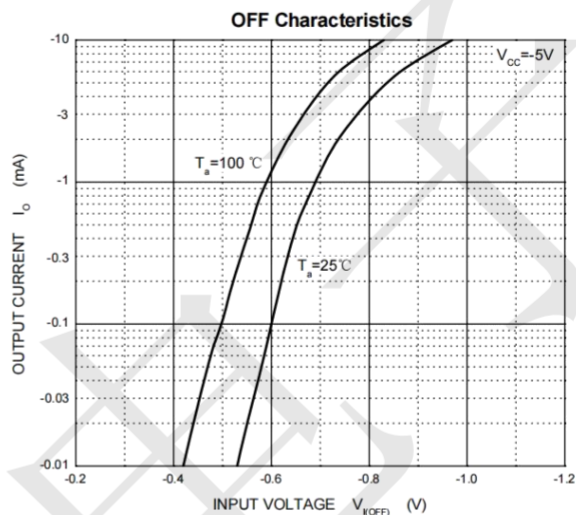
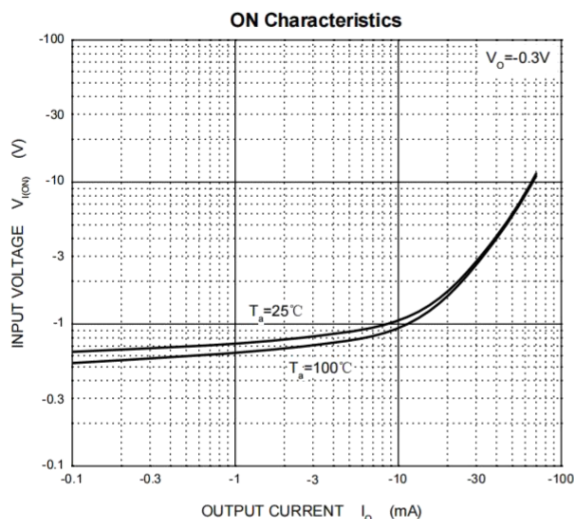
(TA=25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Input voltage	$V_{I(off)}$	$V_{CC}=-5V, I_O=-100\mu A$	-0.5	--	--	V
	$V_{I(on)}$	$V_O=-0.3V, I_O=-10mA$	--	--	-2.0	V
Output voltage	$V_{O(on)}$	$I_O/I_I=-10mA/-0.5mA$	--	--	-0.3	V
Input current	$I_I$	$V_I=-5V$	--	--	-1.8	mA
Output current	$I_{O(off)}$	$V_{CC}=-50V, V_I=0$	--	--	-0.5	$\mu A$
DC current gain	$G_I$	$V_O=-5V, I_O=-10mA$	30	--	--	--
Input resistance	$R_1$		0.7	1.0	1.3	k $\Omega$
Resistance ratio	$R_2/R_1$		0.8	1.0	1.2	--
Transition frequency	$f_T$	$V_O=-10V, I_O=-5mA,$ $=100MHz$	--	250	--	MHz

Note:

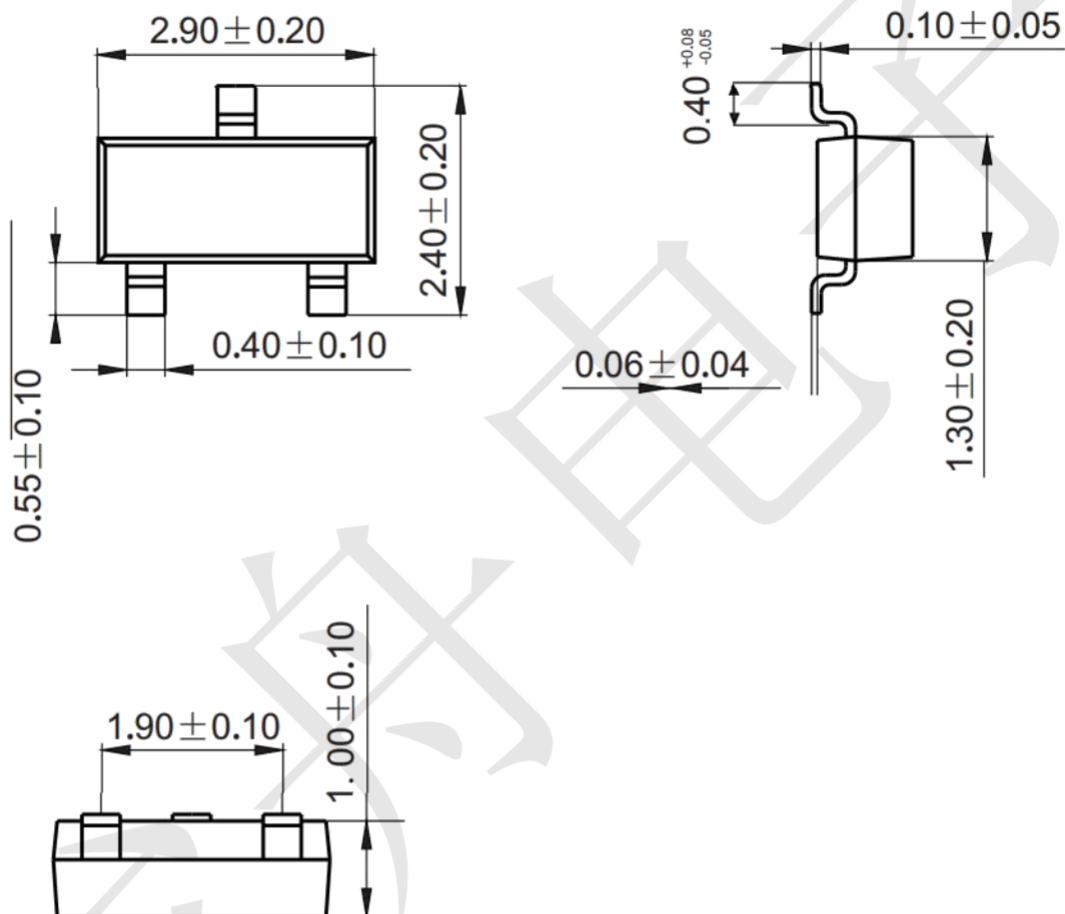
- 1.Characteristics of built-in transistor
- 2.Each terminal mounted on a reference land

### Typical Performance Characteristics(TA=25°C)



### Package Outline Dimensions (unit: mm)

SOT-23



### Mounting Pad Layout (unit: mm)

